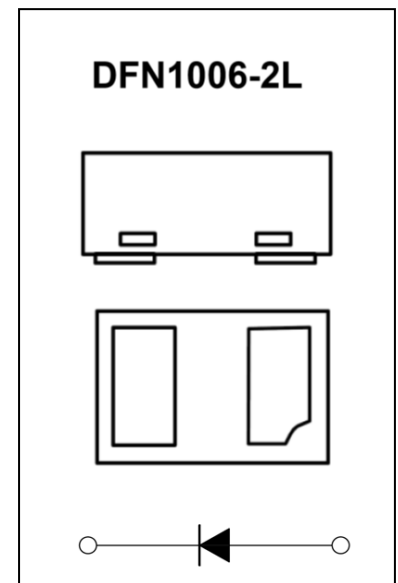


DS5551V-30 Schottky Barrier Diode
Feature

- Small Power Mold Type
- Low VF
- Low IR
- High Reliability

Application

- High Frequency Inverters
- Free Wheeling
- Polarity Protection Applications


MARKING:


Front Side

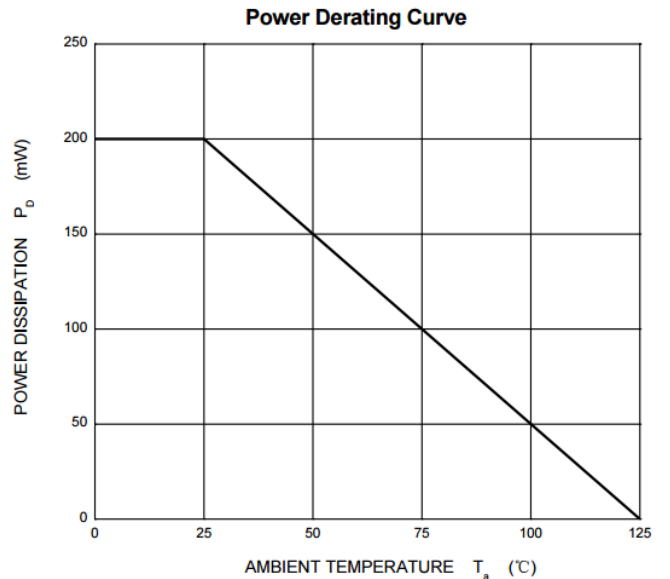
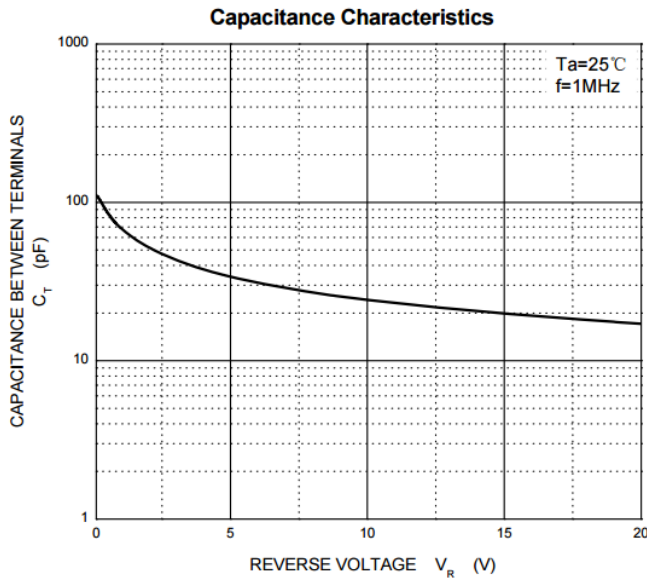
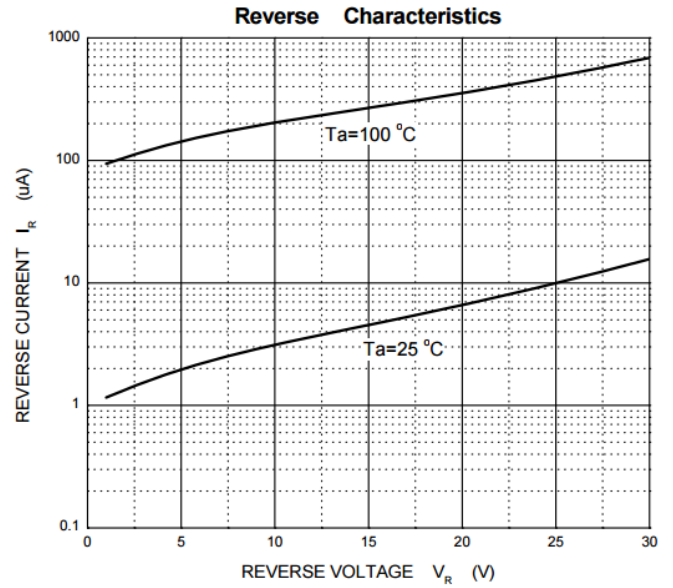
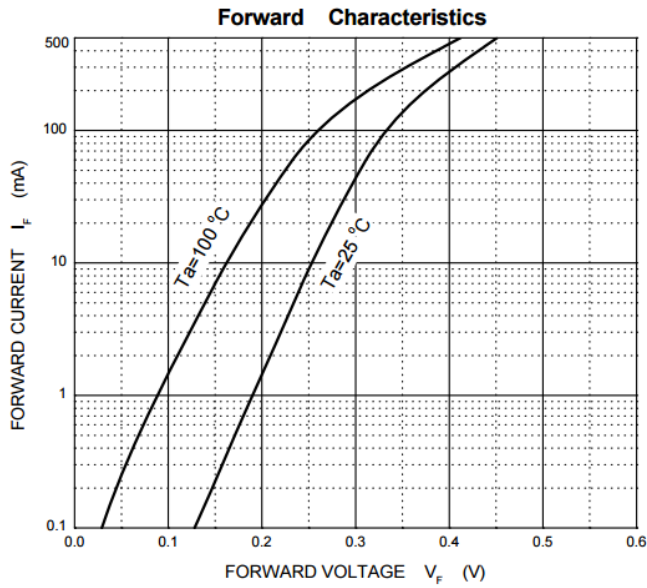
ABSOLUTE MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

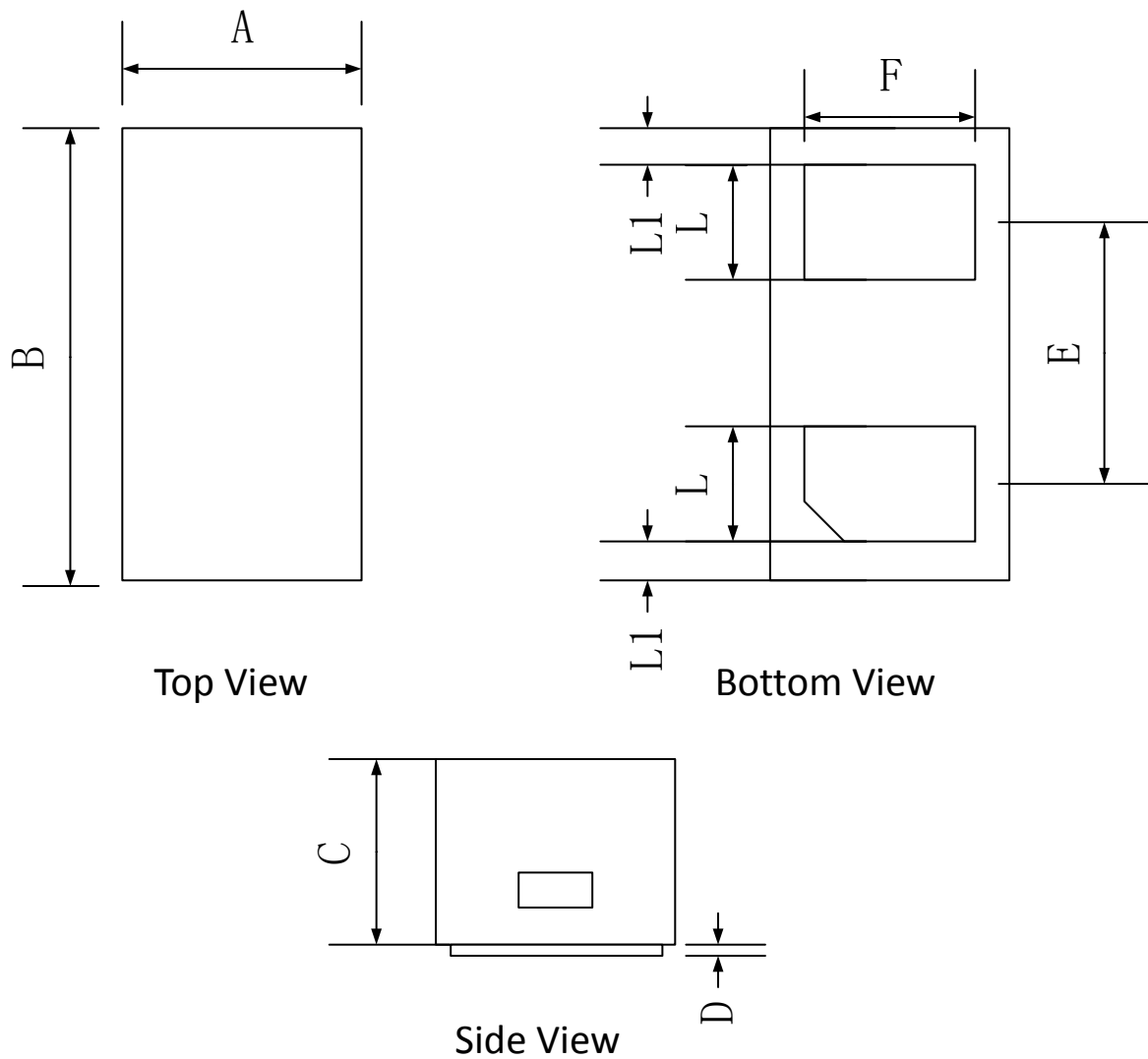
Parameter	Symbol	Value	Unit
DC reverse voltage	V _R	30	V
Mean rectifying current	I _O	0.5	A
Non-repetitive Peak Forward Surge Current @ t=8.3ms	I _{FSM}	2	A
Power Dissipation	P _D	0.1	mW
Thermal Resistance from Junction to Ambient	R _{θJA}	100	°C/W
Junction Temperature	T _J	125	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V _{BR}	I _R = 100uA	30			V
Forward voltage	V _F	I _F = 0.1A			0.36	V
		I _F = 0.5A			0.47	V
Reverse current	I _R	V _R = 20V			100	μA
Diode capacitance	C _D	V _R = 4V, f = 1MHz		20		pF

Typical Characteristics



DFN1006-2L Package Outline Dimensions


	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	0.55	0.60	0.68
B	0.95	1.00	1.08
C	0.44	0.47	0.50
D	0.00	0.03	0.05
E	-	0.65	-
F	0.40	0.50	0.60
L	0.20	0.25	0.30
L1	0.05REF		

单击下面可查看定价，库存，交付和生命周期等信息

[>>GP\(格瑞宝\)](#)